

Broadband solar absorption with silicon metamaterials driven by strong proximity effects

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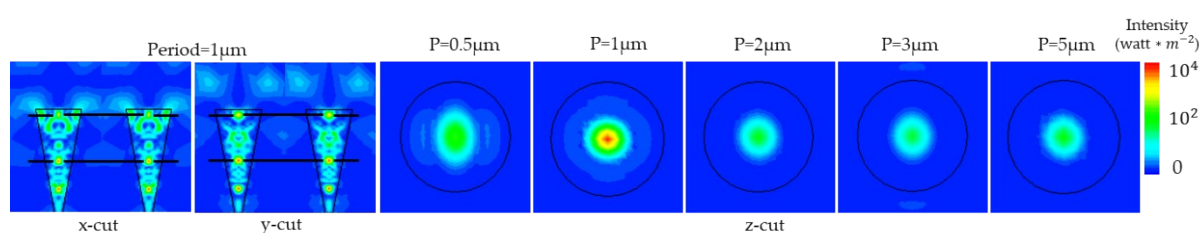
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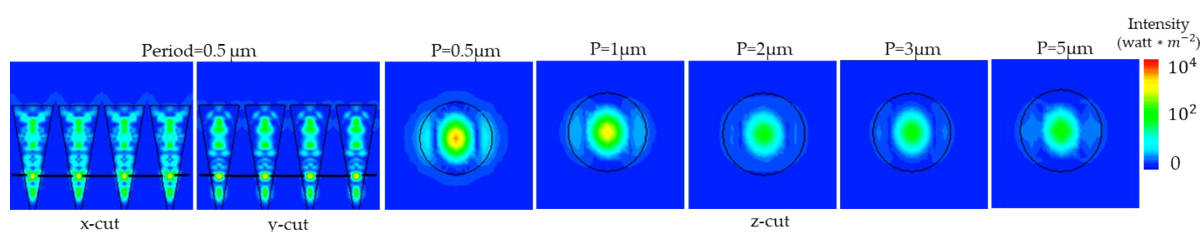
Supplementary information

Figure 1

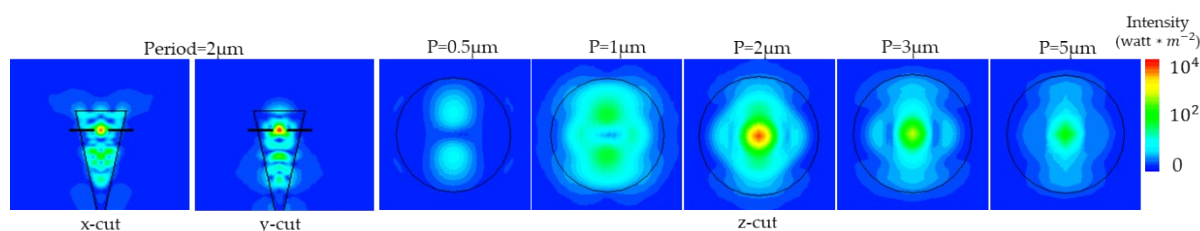
Peak 2: $\lambda=500$ nm (maximum Q_{abs} for $P=1\ \mu\text{m}$)



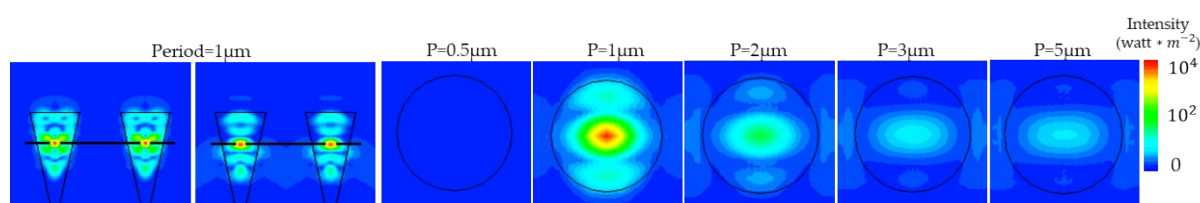
Peak 3: $\lambda=540$ nm (maximum Q_{abs} for $P=0.5\ \mu\text{m}$)



Peak 6: $\lambda=740$ nm (maximum Q_{abs} for $P=2\ \mu\text{m}$)



Peak 7: $\lambda=820$ nm (maximum Q_{abs} for $P=1\ \mu\text{m}$)



Peak 8: $\lambda=980$ nm (maximum Q_{abs} for $P=0.5 \mu\text{m}$)

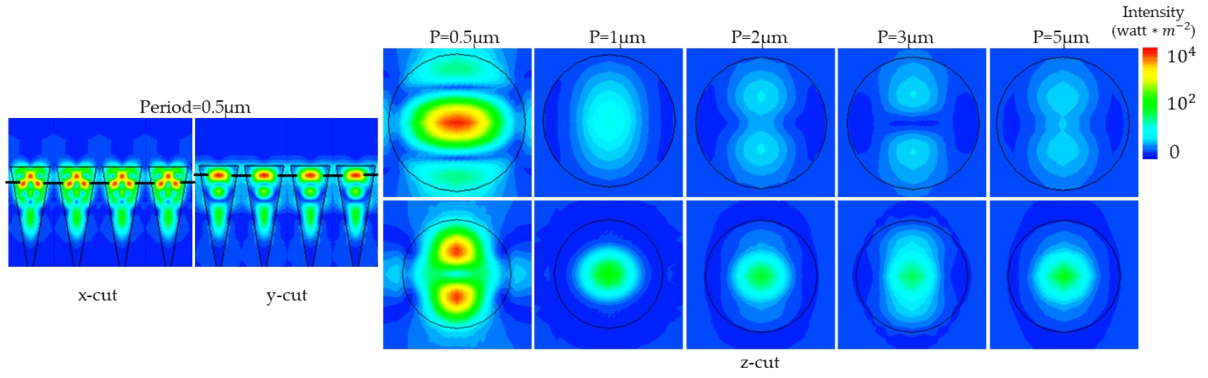


Figure 2

